

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SD1632

DESCRIPTION

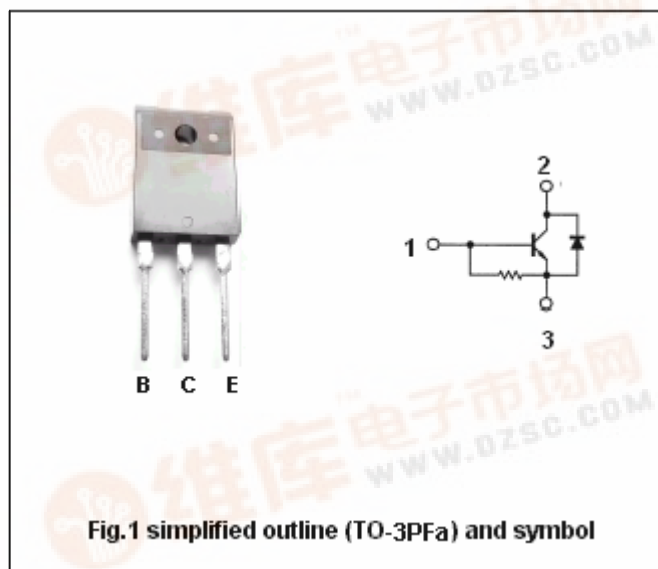
- With TO-3PFA package
- High voltage ,high speed
- Built-in damper diode
- Wide area of safe operation

APPLICATIONS

- For horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		4	A
I_{CM}	Collector current-peak		15	A
I_{BM}	Base current		3.5	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	70	W
T_j	Junction temperature		130	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~130	$^{\circ}\text{C}$

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CHARACTERISTICS

 $T_j=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=500\text{mA}; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=3\text{A}; I_B=1\text{A}$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=3\text{A}; I_B=1\text{A}$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=750\text{V}; I_E=0$			50	μA
		$V_{CB}=1500\text{V}; I_E=0$			1	mA
h_{FE}	DC current gain	$I_C=3\text{A}; V_{CE}=10\text{V}$	5		15	
V_F	Diode forward voltage	$I_C=-4\text{A}$			2.2	V
Switching times						
t_{stg}	Storage time	$I_C=3\text{A}$ $I_{Bend}=1\text{A}; L_{Leak}=5\mu\text{H}$	4		9	μs
t_f	Fall time				0.8	μs

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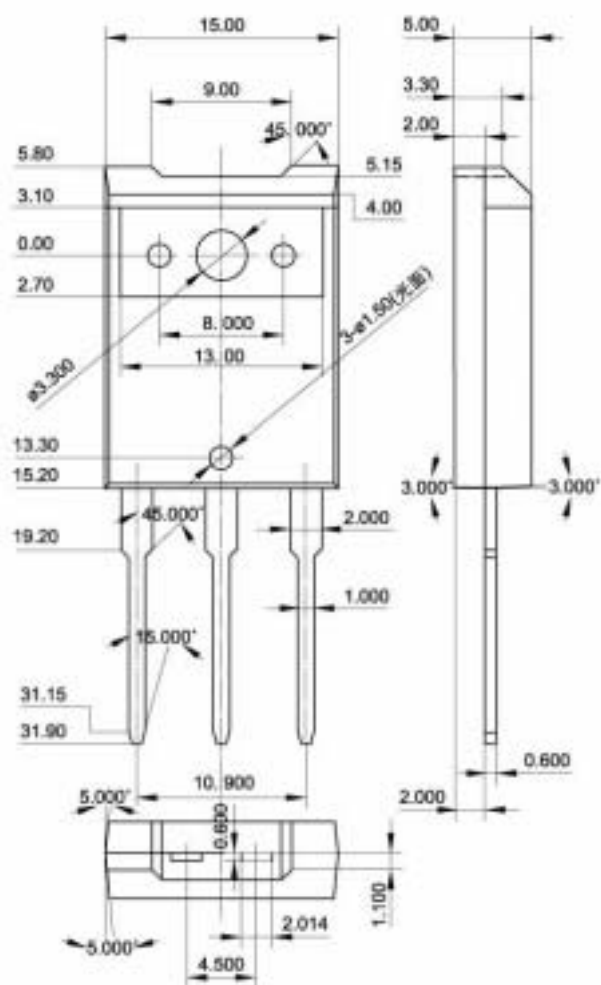


Fig.2 Outline dimensions (unindicated tolerance: $\pm 0.30\text{mm}$)